

isc Silicon NPN Power Transistor

2SD732

DESCRIPTION

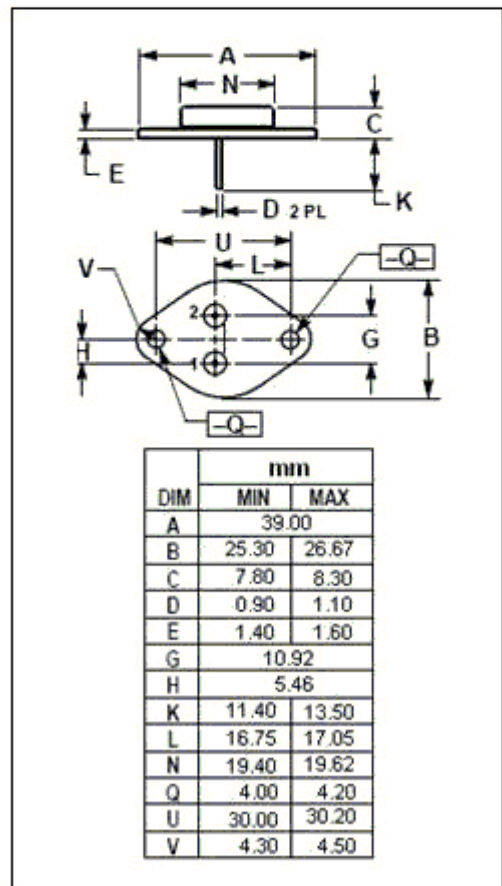
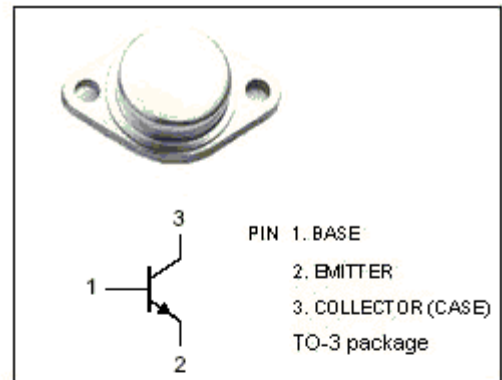
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 120V$ (Min)
- High Current Capability
- Complement to Type 2SB696

APPLICATIONS

- Designed for AF power amplifier applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	MAX	UNIT
V_{CBO}	Collector-Base Voltage	150	V
V_{CEO}	Collector-Emitter Voltage	120	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	8	A
I_{CM}	Collector Current-Peak	12	A
P_C	Collector Power Dissipation @ $T_C=25^{\circ}C$	80	W
T_j	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-40~150	$^{\circ}C$



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ELECTRICAL CHARACTERISTICS

 $T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=5\text{mA}; R_{BE}=\infty$	120			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C=5\text{mA}; I_E=0$	150			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=5\text{mA}; I_C=0$	6			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=5\text{A}; I_B=0.5\text{A}$		0.6		V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C=1\text{A}; V_{CE}=5\text{V}$			1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=80\text{V}; I_E=0$			0.1	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=4\text{V}; I_C=0$			0.1	mA
h_{FE}	DC Current Gain	$I_C=1\text{A}; V_{CE}=5\text{V}$	40		320	
f_T	Current-Gain—Bandwidth Product	$I_C=1\text{A}; V_{CE}=5\text{V}$		15		MHz

◆ h_{FE} Classifications

C	D	E	F
40-80	60-120	100-200	160-320